# M agnetoconductivity of H ubbard bands induced in Silicon M O SFETs

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#### A bstract

Sodium impurities are di used electrically to the oxide-sem iconductor interface of a silicon M O SFET to create an impurity band. At low temperature and at low electron density, the band is split into an upper and a lower sections under the in uence of C oulom b interactions. W e used m agnetoconductivity m easurements to provide evidence for the existence of H ubbard bands and determ ine the nature of the states in each band.

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#### 1 Introduction

In the early 70's a substantial e ort was put into the study of the e ect of impurities in silicon MOSFETs. The main reason for this was to understand the origin of the instabilities in eld e ect transistors and the umpredictable changes in the threshold voltages. These studies contributed to improve the performance of a new generation of silicon-based chips for computer applications and their reliability. In fact, the presence of impurities or defects in the silicon oxide leads to an inhom ogeneity in the electron distribution at the Si-SiO<sub>2</sub> interface and traps electrons. The most common impurities are alkali metals like lithium, potasium or sodium. These trap states give rise to the

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form ation of an impurity band below the conduction band. This e ect was rst observed by Fang, Hartstein and Pepper [,2,3] for high im purity concentrations  $(> 1 \quad 10^{12} \text{ cm}^{-2})$ . A consequence of the existence of such an impurity band is that the onset voltage for conduction in oxide-doped M O SFETs is also shifted and the electron mobility substantially decreased. The impurity band produced by such a doping can be described by tight-binding models for high in purity density [4] whereas M ott-H ubbard m odels [5] need to be used for the low concentrations for which C oulom b interaction plays a de ning role. G iven single valency atoms like sodium, it would be expected that the electronic states in the band are made of single trapped electrons. Under the in uence of electron-electron interactions, it has been suggested how ever that a stable state with two bound electrons would exist and would be characterized by a long lifetime (D state) [6,7]. The band form ed by the D states is referred as the upper Hubbard band (UHB) and the one formed with neutral states as the lower Hubbard band (LHB). The question of the existence of Hubbard bands in Silicon MOSFETs has been put forward by Mott nearly thirty years ago to explain the magnetoconductivity of short disordered MOSFETs but the bands were never directly observed in experiments [8]. The study of Hubbard bands in sem iconductors has regained som e attention since the end of the 90's with the development of quantum information and quantum computation [9]. Following the di culty in reading out directly the value of the spin in architectures developed in agreement with the Kanemodel, a spin to charge conversion was proposed. In this approach a stable D state is used to read out the result of the quantum operations. Som e optical studies have previously been carried out in M ott-H ubbard insulators like Sr<sub>2</sub>CuO<sub>3</sub> [10] or boron-doped diam ond [11] but no direct conductivity measurem ent has been performed so far. In the present paper, we have used magnetoconductivity m easurem ent to provide direct evidence of the presence of H ubbard bands in a sodium -doped silicon MOSFET.We also describe the electronic con quration of the obtained D state by distinguishing between  $1s^2$ , 1s2s and 1s2p states.

### 2 Experiment

All m easurements were performed on silicon MOSFETs. Such devices have been widely used because of the ability to continuously vary the electron density and the Ferm i energy by use of a metal gate. The geometry of the device was chosen to be circular (C orbino geometry) to avoid leakage current paths around the source and drain contacts. The devices were fabricated using a high resistivity ( $10^4$  .cm) (100) p-silicon wafer to minimize, as much as possible, the scattering with boron acceptor impurities, especially close to the siliconoxide interface. A 35 nm thick gate therm aloxide was grown at 950 C in a dry,



Fig.1.a) C ross section view of a corbino M O SFET used in the experiment when the sodium ions are close to the Si-SiO<sub>2</sub> interface.b) Schematic diagram of the density of states (DOS) for the present device, with a low energy (LHB) and a high energy (UHB) impurity band separated by a gap to the conduction band (CB).

chlorine-free oxygen atm osphere. The sidewalls of the oxide were protected by thick insulating LOCOS (LocalOxidation of Silicon). The e ective gate length of the Corbino MOSFETs was 1 m and the diameter of the interior contact was 110 m. Contacts were realized by implanting phosphorous at high dose and sputtering alum inium. The contact resistivity wasm easured to be 3.5 and 2.3 cm<sup>1</sup> at nitrogen and helium temperatures, respectively, and the sheet resistance was 6.3 and 5.9  $2^{1}$  for the same tem peratures. Sodium ions were introduced onto the oxide surface by immersing the device in a 10  $^7$  N solution 10<sup>11</sup> cm<sup>2</sup>) of high-purity sodium chloride in deionized water. The ( 6:4 surface of the chip was then dried with nitrogen gas and an alum inium gate subsequently evaporated. The application of a positive gate voltage (+ 4V at 65 C for 10 m ins) causes the sodium ions to drift towards the  $SiSiO_2$  interface while the application of 4V DC in the same conditions rem oves the ions from the interface. The ions are frozen at their position once the device tem perature becomes lower than approximately 150K (Fig. 1). Standard low-noise lock-in techniques with an ampli ergain of  $1^{\circ}$  V/A were used to measure the source to drain conductivity. An AC excitation of am plitude  $V_{AC} = 15$  V and a frequency of 11 H z were chosen. The D C o set of the ampli er was suppressed using an appropriate blocking capacitor. The gate voltage was controlled by a high resolution digital to analog converter and the tem perature measured by a calibrated germ anium therm on eter. The magnetic eld was produced by an 0 xford 12 T superconducting m agnet and applied perpendicular to the Si-SiO<sub>2</sub> interface.

Several devices were processed identically and gave results that lead to iden-

tical conclusions although we noticed som e variation in the relative position and width of the impurity bands, as well as in the conductivity values. From the di erence in the threshold voltage at 77K, we obtained an e ective ion density of 3:7  $10^{11}$  cm<sup>2</sup> at the interface indicating that only 60% of the ions drifted to the interface. We also fabricated a number of control devices that were not exposed to sodium contam ination and were used for comparison. The following results are presented for a speci c device that was chosen for its high reproducibility in time as well as for its high signal to noise ratio.

# 3 Results and discussion

Fig. 2a represents the source-drain conductivity obtained at dimentivalues of the magnetic med. The dependence of conductivity on temperature for the same device in the hopping regime showed the presence of two groups of peaks clustered around  $V_g = 2$  and 0.5V. These were attributed to a split impurity band due to the presence of sodium impurities at the Si-SiO<sub>2</sub> interface [12]. A rguments in favour of Hubbard bands were provided by studying the variation of conductivity at higher temperature, where activation mechanisms determine the behaviour [13].

# 3.1 Negative magnetoconductivity

The magnetoconductivity was found to be negative for the whole range of gate voltages studied. This is expected and was already observed in localized system s [14,15,16] (Fig.2b). The variation with magnetic eld is well described by ln B<sup>2</sup> even at elds up to 5T where is gate voltage dependent. This behaviour is often attributed to an orbital compression of the donor wavefunctions due to the magnetic eld. This results in a reduction of the wavefunction overlap between neighbouring hopping sites and an increase of the localization of electrons [17]. The wavefunction then acquires a phase factor  $(r^3)^{1=2} = l_B^2$  where  $l_B$  is the magnetic length given by  $l_B = (\sim = B)^{1=2}$ , r is the hopping length and is the localization length. This assumes a gaussian distribution for the ux . For transport processes involving only one hop within an area  $(r^3)^{1=2}$  as in the case of nearest-neighbour hopping or resonant tunneling, ln is found to be quadratic in magnetic eld with given by [8]:

$$= \frac{1}{12} \frac{B_{c}}{2} \frac{e^{2}}{e^{2}N_{T}^{3=2}}$$
(1)



Fig. 2.a) Conductivity versus gate voltage at B = 0T, 2.5T and 5T (from top to bottom) at 309m K.For clarity curves are separated by a constant o set of 10<sup>-3</sup> e<sup>2</sup>=h. b) M agnetoconductivity for  $V_g = 0.24$  (), 0.56 (), 0.97V (?) and 2.08V (/).

N $_{\rm T}$  is the density of active traps and B $_{\rm c}$  is a constant describing the number of bonds in a circular percolation problem, being in tunnelling problem s and respectively 4.5 and 2.7 in the case of nearest-neighbour hopping in a zero or

nite width impurity band. If, however, the transport is described by several hops, a minimization procedure, as rst used by M ott, [9] needs to be carried out in order to nd the optimum hopping length and hopping energy. This makes temperature dependent [20].

$$= \frac{1}{24} \frac{e^{2}}{e^{-2}} \frac{4}{(p+3)^{3}} \frac{1}{T} \frac{T_{0}}{T}$$
(2)

where p is 0 in case of the M ott variable range hopping regime [21] or 1 in case electron correlations are important (E fros and Shklovskii regime [22])

### 3.2 Low tem perature conductivity and localization length

The proper analysis of (B) is thus constrained to the correct description of the transport mechanism at low temperature. Below 1K, the conductivity decreases rapidly with temperature as = (T) (0) T<sup>2:7</sup> (Fig. 3a). This variation is not a ected by the source-drain voltage and  $eV_{AC} < k_B T$  in all measurements (Fig. 3b). Consequently, we do not expect that this behaviour results from electron heating in the contacts, but from a contribution of the acoustic phonons at low temperature. In our previous study, the same data



Fig. 3. a) Variation of the conductivity in temperature for  $V_g = 0.24$  (), 0.56 (), 0.97V (?) and 2.08V (/).b) Variation of the temperature exponent with  $V_{AC}$  at the same gate voltages.c) Variation of the localization length in term s of  $V_g$  at 309m K deduced from Eq.2.

was analyzed in temperature and we showed that the transport was characterized by hopping conduction with an exponent p 0:4 above 1K [12]. In the fram ework of 2D resistance networks [23] the conductivity is =Τ, whereas the scattering time is  $\hat{r} = T$  where is the hopping rate and r the hopping length. 0 ur results show ed the best ts were obtained with an exponential prefactor T<sup>0.8</sup>. This im plies varies as T<sup>1.6</sup>. This value is close to the T<sup>3=2</sup> law expected in non-polar sem iconductors for acoustic phonon scattering [24] and as observed in silicon [25]. This excellent agreem ent with theory in plies that acoustic phonon-assisted hopping is the main mechanism for transport above 1K and that this transport is in fact still active and predom inant at 300 mK. Due to the short hopping distance, typically r 3, an electron is scattered by only a few in purities between the initial and the nal sites. Consequently, Eq. 2 should be used with p = 0.4 to estimate the at low tem perature, giving the values of  $T_0$ value of the localization length from our previous analysis [12]. Results are shown on Fig. 3c. The variation of  $(V_{\alpha})$  is consistent with our previous observations, i.e. an increase in the localization at the band positions, but the values are now nearly half of those

has already been observed experimentally in insulating devices with strong spin-orbit coupling [26]. It is plausible that such an elect takes place in our device because of the presence of strong potential uctuations at the  $SiSiO_2$ interface. We also observed that the conductivity of the lower band is suppressed at a eld of about 3.5 T whereas the upper band is still conducting even at the higher eld. This suggests that the lower band is energically deeper and is already strongly localized even in the absence of a magnetic eld. E ffectively, the upper band is supposed to be closer to the extended states in energy than the lower band and it is likely to be more strongly in uenced by the enhancem ent of the localization due to the shrinkage of the electron

obtained from  $T_0$  () in the absence of magnetic eld 12]. Such a halving of

wave function caused by the magnetic eld. A point of interest is the absence of signi cant di erences in the values of the localization length in the upper and lower bands. One may expect indeed the lower band to be more deeply localized and have a lower localization length. In fact, one needs to consider that, in our device and because of disorder, the lower Hubbard band may be formed by a majority of singly occupied states and a minority of empty or doubly-occupied states. In order to get transport through the lower Hubbard band, most of the electrons will hop to a singly-occupied state and form a D state. On the other hand, in the upper Hubbard band, most of the sites will be doubly-occupied and the electrons will hop directly to the conduction band edge because of the presence of a large conduction band tail and the presence of states in the gap between the upper Hubbard band and the conduction band. A s a consequence, we expect to due the same localization length for the upper and lower band in transport measurement in the hopping regime.

# 3.3 Magnetoconductivity uctuations

We observed also a non-monotonic decrease in the conductivity with maqnetic eld. This takes the form of uctuations with amplitude dependent on gate voltage. These uctuations are present in m any devices except for those without sodium ions. The uctuations appear as a series of positive and negative m agnetoconductivities. Their position in m agnetic eld also changes with time, but in general is periodic in B. Such uctuations have already been observed by N guyen [27] and were attributed to random interference between different hopping paths. To proceed with the analysis, them agnetic eld value  $B_m$ of the uctuation extrem a were extracted from the curve (B) = (B)  $exp(B^2)$  and plotted as a function of the extrem a index (Fig. 4). We found a linear dependence with a slope B for all gate voltages indicating the uctuations are periodic in magnetic eld. To minimize the uncertainty due to the limited number of points, the experiment was repeated four times with the same con quration. We found that =  $(\sim = eB)^{1=2}$  but  $(r)^{1=2}.We$ can deduce the modulation corresponds to an integer number of elementary ux quanta through a surface of a rear r and that  $\mathbb{R}_{h}$  is given by :

$$B_{m} = \frac{nh}{2 \text{ er}}$$
(3)

This situation is similar to that giving rise to A haronov-Bohm oscillations in quantum dot systems [28] with (r)<sup>1=2</sup> playing the role of the dot radius. In the hopping regime, the interference area has a cigar-shape with radius in one direction and the hopping length in the hop direction. Quantum interferences between forward and backscattering paths induced by the localizing in purity



Fig. 4.M easure of the critical eld of the uctuations and the corresponding values for  $V_q = 0.43 V$ , 0.56 V, 1.50 V and 2.08 V at 309 m K.

potential due to the magnetic eld may be responsible for such uctuations.

## 4 Peak positions in magnetic eld

Finally, we discuss the variation in the position of the peaks in magnetic eld (Fig. 5). We observed that the group of peaks clustered in the upper band moves towards more negative gate voltages with approximately a slope of 4mV/T whereas the one in the lower band move with a slope of 4mV/T. Such movement in energy levels are expected in magnetic eld, and the di erence in the sign can be explained by including the elect of the orbital momentum. In fact, this behaviour cannot be interpreted as being due to spine ects as no spin splitting was observed. A lso, the gap energy between the upper and lower bands estimated previously [13] is much larger than the spin splitting at 5T. For simplicity, we suppose the electrons are localized at the impurity sites with an approximate parabolic potential of width  $!_0$ . The variation E of an energy level is then described by [29,30]:

$$E = (2n + jlj + 1) \sim \frac{4}{4} \frac{\frac{!_{c}^{2}}{!_{c}^{2}} + !_{0}^{2}}{4} \frac{!_{0}^{5}}{!_{0}^{5}} \frac{1}{2}l \sim !_{c}$$
(4)

where n is the index for the Landau levels, l is the value of the angular momentum and  $!_c = eB = m$  with  $m = 0:19m_e$  the transverse e ective mass of the electrons in < 100 > silicon.



Fig. 5. C onductivity versus gate voltage and m agnetic eld at 309 mK.

Consequently, n = 0 and l = 0 are associated with the lower group of peaks (non-degenerate) and n = 1 and l = 1 to the upper group (degeneracy of 2). The value l = 1 also implies the presence of two electrons in the con guration ls2p. This behaviour supports the idea of the form ation of H ubbard bands [31] and a stable N a ion at the SiSiO<sub>2</sub> interface as well as the presence of a strong spin-orbit coupling. This shows as well the importance of C oulom b interactions in this system . When increasing the magnetic eld, the wave-function of the low est state shrinks and the interaction between the two degenerate electrons grows until the Zeem an energy is su cient to spin- ip the second electron and prom ote it to the l = 1 state. This transition is predom inantly caused by C oulom b interactions since no spin splitting was observed and was still quite sm all even at 5T. Finally, the 1s2p con guration holds as long as E < 0 for the upper band, which is veried up to 5T. This implies that  $\sim !_0 > 2:7m$  eV and provides a lower bound for the mean in purity potential depth.

## 5 Conclusion

We have observed a negative magneto-conductivity up to 5T. This result conms previous observations on the same device that the system is strongly localized with a localization length of the order of the mean distance between impurities. The uctuations observed in the magnetoconductivity have been attributed to quantum interference due to the presence of impurity centres close to the interface. Finally, the shift in the position of the bands are compatible with the presence of upper and lower Hubbard bands and a possible transition from a singlet to a triplet state in the upper band induced by electron-electron interaction. A cknow ledgem ent

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